
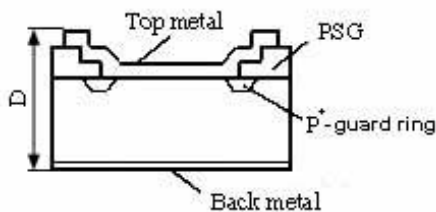
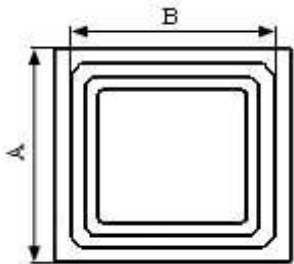


		5A/60V. Die Size-69mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort	
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	60	65	
Average Rectified Forward Current	$I_{F(AV)}$	A	5,0	-	
DC Forward Voltage @ 25°C, $I_F=5,0\text{A}$	$V_F$	V	0,61	0,59	
Maximum Reverse Current @ 25°C, $V_R=60\text{V}$ @ 25°C, $V_R=65\text{V}$ @ 125°C, $V_R=60\text{V}$	$I_R$	mA	0.100 - 45,0	0,080 0,100 40,0	
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	125	-	
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., $T_J<150^\circ\text{C}$ .	$I_{RRM}$	A	3,0		
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)		
Voltage Rate of Change	dV/dt	V/µS	10.000		
Operating Junction Temperature	$T_J$	°C	150		



DIM	ITEM	µm
A <sub>x</sub> A <sub>y</sub>	Wafer Form Die Size	1750
B <sub>x</sub> B <sub>y</sub>	Top Metal Size	1610
D	Thickness	300max.
	Scribe line Width	80

Top metal:

- a) **Al** – for Wire Bonding;
- b) **Al-Ni-Ag** – for Soldering.

Backside metal: **Ti-Ni-Ag**.